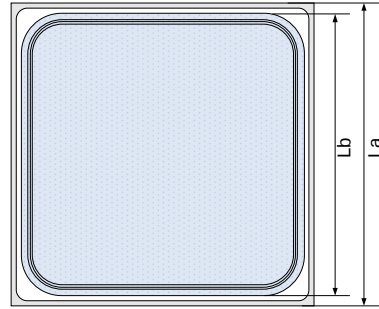


2SB023040MLJY SCHOTTKY BARRIER DIODE CHIPS

DESCRIPTION

- Ø 2SB023040MLJY is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size: 230μm X 230μm;
- Ø Chip Thickness: 155±20μm



Chip Topography and Dimensions

La: Chip Size: 230μm;

Lb: Pad Size: 140μm;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB023040MLJY	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	40	V
Average Forward Rectified Current	IFAV	30	mA
Peak Forward Surge Current@8.3ms	IFSM	200	mA
Maximum Operation Junction Temperature	TJ	125	°C
Storage Temperature Range	TSTG	-40~125	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=0.1mA	40	--	V
Forward Voltage	VF	IF=1mA	--	0.37	V
Reverse Current	IR	VR=30V	--	0.5	μA